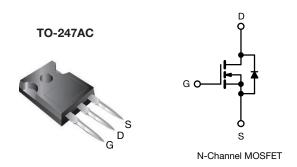
Vishay Siliconix

HALOGEN

FREE

EF Series Power MOSFET With Fast Body Diode



PRODUCT SUMMARY				
V _{DS} (V) at T _J max. 650				
R _{DS(on)} typ. (Ω) at 25 °C	V _{GS} = 10 V 0.059			
Q _g max. (nC)	77			
Q _{gs} (nC)	19			
Q _{gd} (nC)	16			
Configuration	Single			

FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) Ron x Qg
- Low effective capacitance (Co(er))
- · Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



- · Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and halogen-free	SiHG068N60EF-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	600	V
Gate-source voltage			V_{GS}	± 30]
Continuous drain current (T _{.I} = 150 °C)	V _{GS} at 10 V	$T_C = 25 ^{\circ}C$ $T_C = 100 ^{\circ}C$	1	41	
Continuous drain current (1j = 150 °C)	V _{GS} at 10 V	T _C = 100 °C	I _D	26	Α
Pulsed drain current a		I _{DM}	115		
Linear derating factor			2	W/°C	
Single pulse avalanche energy ^b			E _{AS}	226	mJ
Maximum power dissipation		P _D	250	W	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Drain-source voltage slope T _J = 125 °C		0.771	100	N//	
Reverse diode dV/dt ^d		dV/dt	50	V/ns	
Soldering recommendations (peak temperature) c	For	10 s		260	°C

- a. Repetitive rating; pulse width limited by maximum junction temperature
- b. V_{DD} = 120 V, starting T_J = 25 °C, L = 28.2 mH, R_q = 25 Ω , I_{AS} = 4 A
- c. 1.6 mm from case
- d. $I_{SD} \le I_D$, di/dt = 210 A/ μ s, starting $T_J = 25$ °C



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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Maximum junction-to-ambient	R _{thJA}	40	°C/W	
Maximum junction-to-case (drain)	R _{thJC}	0.5	G/VV	

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•			
Drain-source breakdown voltage	V _{DS}	V _{GS} =	: 0 V, I _D = 250 μA	600	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Referenc	e to 25 °C, I _D = 1 mA	-	0.63	-	V/°C
Gate-source threshold voltage (N)	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = 250 μA	3	-	5	V
Oala a sana lada a sa		,	/ _{GS} = ± 20 V	-	-	± 100	nA
Gate-source leakage	I _{GSS}	,	$I_{GS} = \pm 30 \text{ V}$	-	-	± 1	μΑ
7		V _{DS} =	480 V, V _{GS} = 0 V	-	-	1	μΑ
Zero gate voltage drain current	I _{DSS}	V _{DS} = 480 V	, V _{GS} = 0 V, T _J = 125 °C	-	-	2	mA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 16 A	-	0.059	0.068	Ω
Forward transconductance	9 _{fs}	V _{DS}	= 30 V, I _D = 16 A	-	9	-	S
Dynamic							
Input capacitance	C _{iss}		V _{GS} = 0 V,	-	2628	-	
Output capacitance	C _{oss}	Ţ,	$V_{\rm DS} = 100 \rm V$	-	122	-	1
Reverse transfer capacitance	C _{rss}		f = 1 MHz		7	-	
Effective output capacitance, energy related ^a	C _{o(er)}	V 0VI 400VV 0V		-	87	-	pF
Effective output capacitance, time related ^b	C _{o(tr)}	V _{DS} = 0 \	$V_{DS} = 0 \text{ V to } 480 \text{ V}, V_{GS} = 0 \text{ V}$		543	-	-
Total gate charge	Qg			-	51	77	
Gate-source charge	Q_{gs}	$V_{GS} = 10 \text{ V}$ $I_D = 16 \text{ A}, V_{DS} = 480 \text{ V}$		-	19	-	nC
Gate-drain charge	Q _{gd}			-	16	_	
Turn-on delay time	t _{d(on)}			-	27	54	
Rise time	t _r	V _{DD} = 480 V, I _D = 16 A,		-	55	83]
Turn-off delay time	t _{d(off)}	V _{GS} =	$10 \text{ V}, \text{ R}_{\text{g}} = 9.1 \Omega$	-	53	80	ns
Fall time	t _f			-	35	70	
Gate input resistance	R_g	f = 1	MHz, open drain	0.3	0.7	1.4	Ω
Drain-Source Body Diode Characteristic	s						
Continuous source-drain diode current	Is	MOSFET sym showing the	bol	-	-	41	
Pulsed diode forward current	I _{SM}	integral reverse p - n junction diode		-	-	115	Α
Diode forward voltage	V _{SD}	T _J = 25 °C	C, I _S = 16 A, V _{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t _{rr}			-	152	304	ns
Reverse recovery charge	Q _{rr}		5 °C, I _F = I _S = 16 A,	-	1	2	μC
Reverse recovery current	I _{RRM}	di/dt = 100 A/µs, V _R = 400 V		-	14	-	A

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

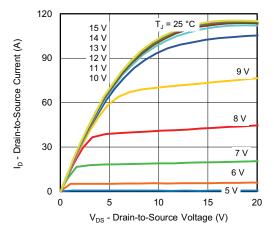


Fig. 1 - Typical Output Characteristics

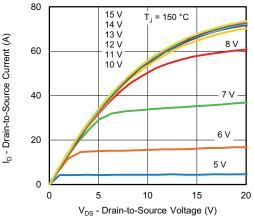


Fig. 2 - Typical Output Characteristics

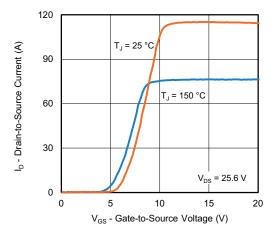


Fig. 3 - Typical Transfer Characteristics

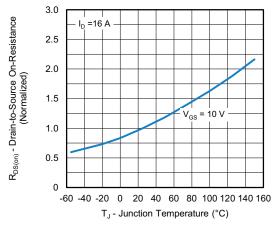


Fig. 4 - Normalized On-Resistance vs. Temperature

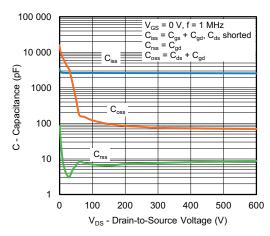


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

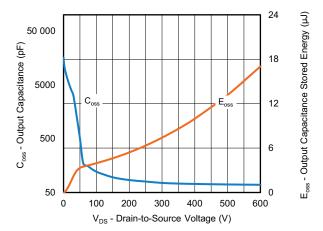


Fig. 6 - Coss and Eoss vs. VDS



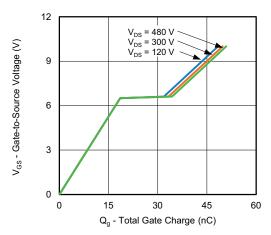


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

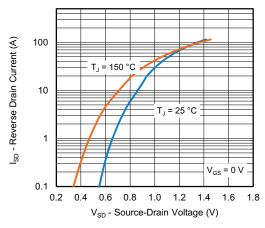


Fig. 8 - Typical Source-Drain Diode Forward Voltage

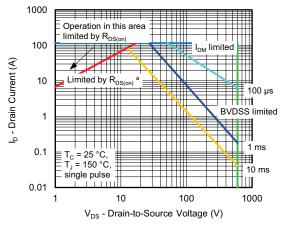


Fig. 9 - Maximum Safe Operating Area



a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

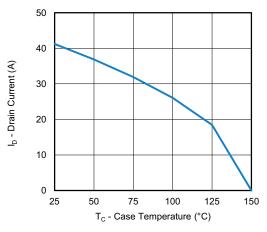


Fig. 10 - Maximum Drain Current vs. Case Temperature

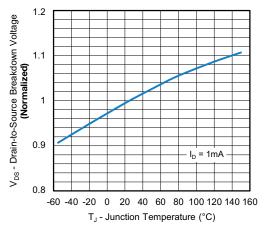


Fig. 11 - Temperature vs. Drain-to-Source Voltage



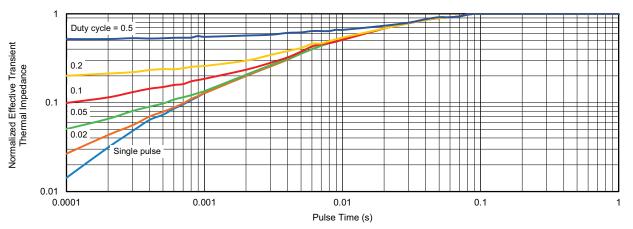


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

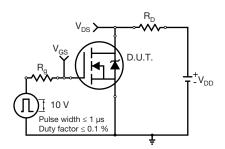


Fig. 13 - Switching Time Test Circuit

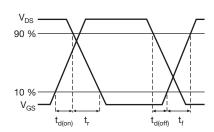


Fig. 14 - Switching Time Waveforms

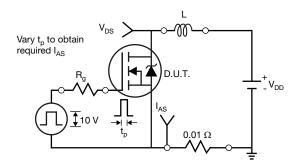


Fig. 15 - Unclamped Inductive Test Circuit

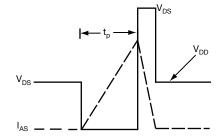


Fig. 16 - Unclamped Inductive Waveforms

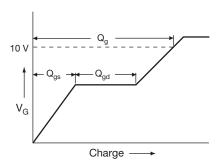


Fig. 17 - Basic Gate Charge Waveform

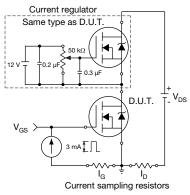
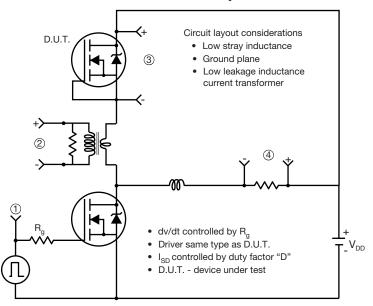


Fig. 18 - Gate Charge Test Circuit



Peak Diode Recovery dv/dt Test Circuit



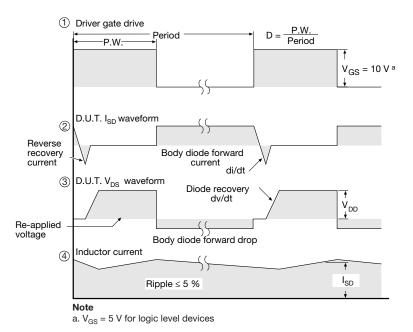


Fig. 19 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?92308.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	0.254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.2	54	
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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